

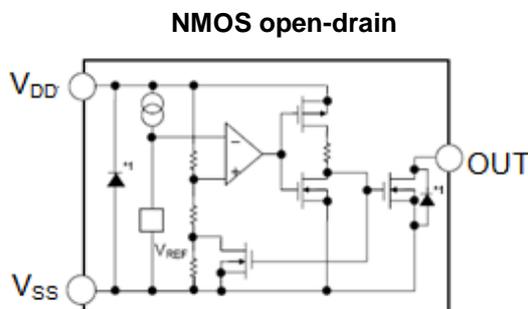
■ INTRODUCTION

The SMV801 Series is a series of high-precision low voltage detectors developed using CMOS process. The detection voltage is fixed internally, with an accuracy of 2.0%. Two output forms, NMOS open-drain and CMOS output, are available.

■ APPLICATIONS

- Memory battery back-up circuits
- Power-on reset circuits
- Power failure detection
- Power monitor for portable equipment such as notebook computers, digital cameras, PDA, and cellular phones
- Constant voltage power monitors for cameras, video equipment and communication devices
- Power monitor for microcomputers and reset for CPUs

■ BLOCK DIAGRAMS



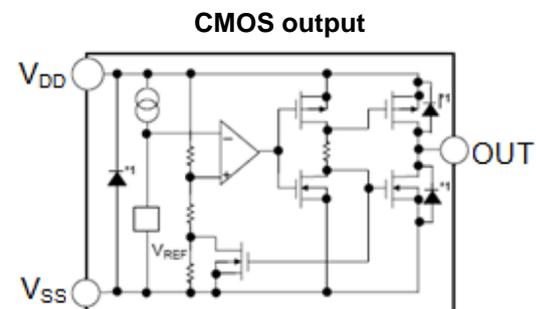
■ FEATURES

- Ultra-low current consumption: 0.9mA @ 3.5V (Typ.)
- High-precision detection voltage: $\pm 2.0\%$
- Operating voltage range: 0.7V ~ 6.0V
- Hysteresis characteristics: $-V_{DET} \times 5\%$ (Typ.)
- Detection voltage: 0.9V ~ 2.0V (10mV step)
- Output forms:
NMOS open-drain output (Active Low)
CMOS output (Active Low)

■ ORDER INFORMATION

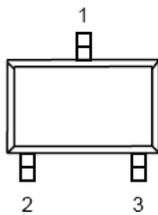
SMV801①②③④⑤

DESIGNATOR	SYMBOL	DESCRIPTION
①	C	CMOS
	N	NMOS open drain
② ③ ④	Integer	Detection Voltage (0.90V~2.00V), “④”elide when it is “0” e.g. 3.0V=② :3, ③ :0 2.93V=② :2, ③ :9, ④ :3
⑤	M/MA/MB/MR	Package: SOT-23,SOT-23-3/5
	N	Package: SOT-343(SC-82)
	P	Package: SOT-89-3
	T/TA	Package: TO-92



■ PIN CONFIGURATION

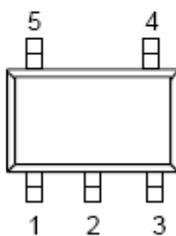
SOT-23-3
Top view



SMV801 Series (SOT-23-3/SOT-23)

PIN NO.	M	MA	MB	FUNCTION
1	V _{DD}	V _{DD}	V _{DD}	Voltage input pin
2	V _{OUT}	-	V _{OUT}	Voltage detection output pin
	-	V _{SS}	-	Ground
3	V _{SS}	-	V _{SS}	Ground
	-	V _{OUT}	-	Voltage detection output pin

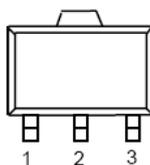
SOT-23-5
Top view



SMV801 Series (SOT-23-5)

PIN NO.	MR	FUNCTION
1	V _{OUT}	Voltage detection output pin
2	V _{DD}	Voltage input pin
3	V _{SS}	Ground
4	NC	No connection
5	NC	No connection

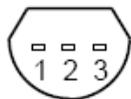
SOT-89-3
Top view



SMV801 Series (SOT-89-3)

PIN NO.	P	FUNCTION
1	V _{OUT}	Voltage detection output pin
2	V _{DD}	Voltage input pin
3	V _{SS}	Ground

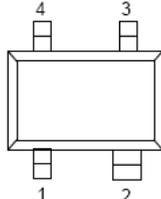
TO-92
Bottom view



SMV801 Series (TO-92)

PIN NO.	T	TA	FUNCTION
1	V _{OUT}	-	Voltage detection output pin
	-	V _{DD}	Voltage input pin
2	V _{DD}	-	Voltage input pin
	-	V _{SS}	Ground
3	V _{SS}	-	Ground
	-	V _{OUT}	Voltage detection output pin

SOT343(SC-82)
Top view



SMV801 Series (SOT-343)

PIN NO.	N	FUNCTION
1	V _{OUT}	Voltage detection output pin
2	V _{DD}	Voltage input pin
3	NC	No Connection
4	V _{SS}	Ground

■ ABSOLUTE MAXIMUM RATINGS

($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNITS
Power supply voltage		V_{DD}	$V_{SS}-0.3 \sim V_{SS} + 8$	V
Output voltage		V_{OUT}	$V_{SS}-0.3 \sim V_{SS} + 8$	V
Power dissipation	SOT-343	PD	250	mW
	SOT-23		250	mW
	SOT-23-3/5		400	mW
	TO-92		500	mW
	SOT-89-3		600	mW
Operating ambient temperature		T_{opr}	$-40 \sim +85$	$^{\circ}\text{C}$
Storage temperature		T_{stg}	$-40 \sim +125$	$^{\circ}\text{C}$
Soldering Temperature & Time		T_{solder}	$260^{\circ}\text{C}, 10\text{s}$	
ESD rating	Human Body Model-(HBM)		2	KV
	Machine Model-(MM)		200	V

■ ELECTRICAL CHARACTERISTICS

($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Detection voltage*1	$-V_{DET}$	—	$-V_{DET(S)} \times 0.98$	$-V_{DET(S)}$	$-V_{DET(S)} \times 1.02$	V
Hysteresis width	V_{HYS}	—	$0.02 \times -V_{DET(S)}$	$0.05 \times -V_{DET(S)}$	$0.08 \times -V_{DET(S)}$	V
Current consumption	I_{SS}	$V_{DD} = -V_{DET} + 0.5\text{V}$	—	1.0	2.0	μA
Operating voltage	V_{DD}	—	0.7	—	6	V
Leakage current	I_{LEAK}	Only for NMOS open-drain output products, $V_{DD} = 8.0\text{V}, V_{OUT} = 8.0\text{V}$	—	—	1.0	μA
temperature coefficient		$T_a = -40^{\circ}\text{C} \sim +85^{\circ}\text{C}$	—	± 120	± 360	ppm/ $^{\circ}\text{C}$
Delay time	T_{PLH}				200	μs

*1. $-V_{DET}$: Actual detection voltage value, $-V_{DET(S)}$: Specified detection voltage value.

■ FUNCTIONAL DESCRIPTION

1. When a voltage higher than the release voltage ($+V_{DET}$) is applied to the voltage input pin (V_{DD}), the voltage will be equal to the input at V_{DD} .

Note that high impedance exists at V_{OUT} with the N-channel open drain configuration. If the pin is pulled up, V_{OUT} will be equal to the pull up voltage.

2. When V_{DD} falls below $-V_{DET}$, V_{OUT} will be equal to the ground voltage (V_{SS}) level (detect state).

Note that this also applies to N-channel open drain configurations.

3. When V_{DD} falls to a level below that of the minimum operating voltage (V_{MIN}) output will become unstable.

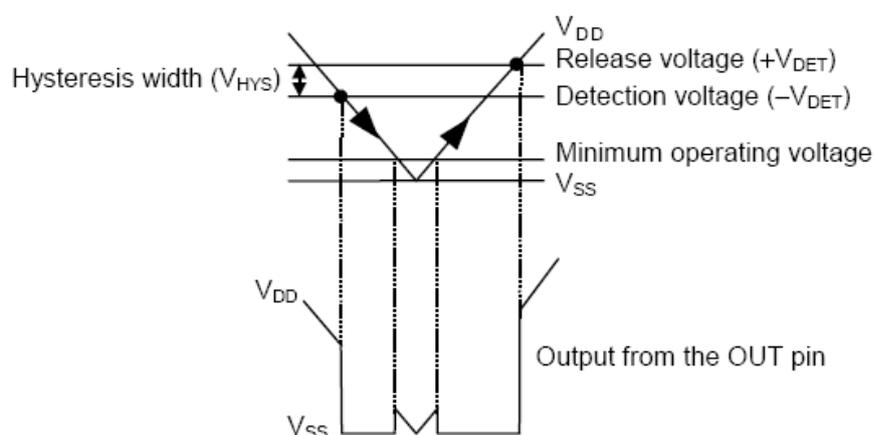
Because the output pin is generally pulled up with N-channel open drain configurations, output will be equal to pull up voltage.

4. When V_{DD} rises above the V_{SS} level (excepting levels lower than minimum operating voltage), V_{OUT} will be equal to V_{SS} until V_{DD} reaches the $+V_{DET}$ level.

5. Although V_{DD} will rise to a level higher than $+V_{DET}$, V_{OUT} maintains ground voltage level via the delay circuit.

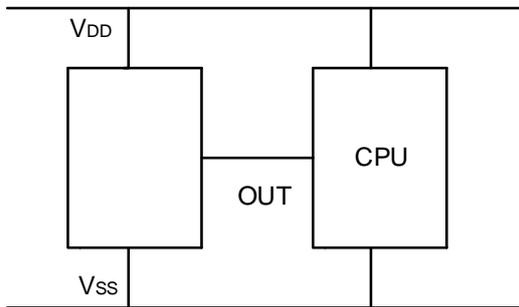
6. Following transient delay time, V_{DD} will be output at V_{OUT} .

Note that high impedance exists with the N-channel open drain configuration and that voltage will be dependent on pull up.

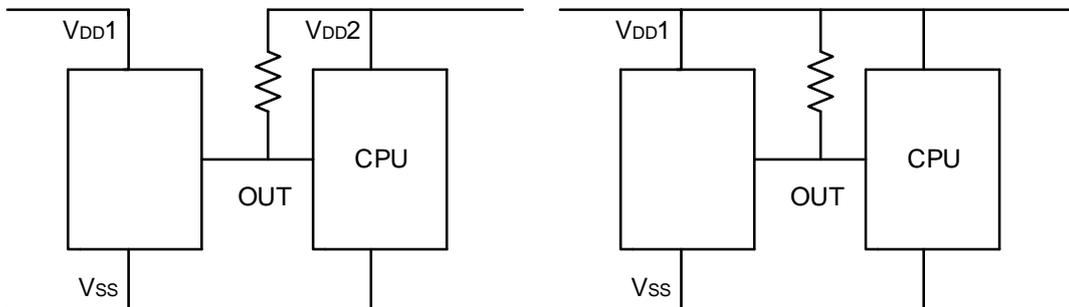


■ TYPICAL APPLICATION CIRCUITS

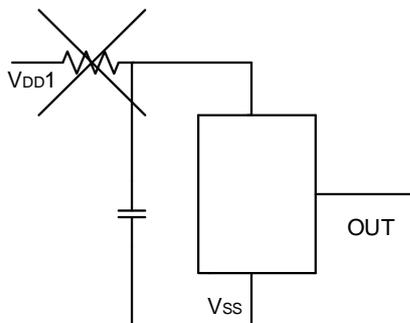
1、CMOS output:



2、NMOS open-drain

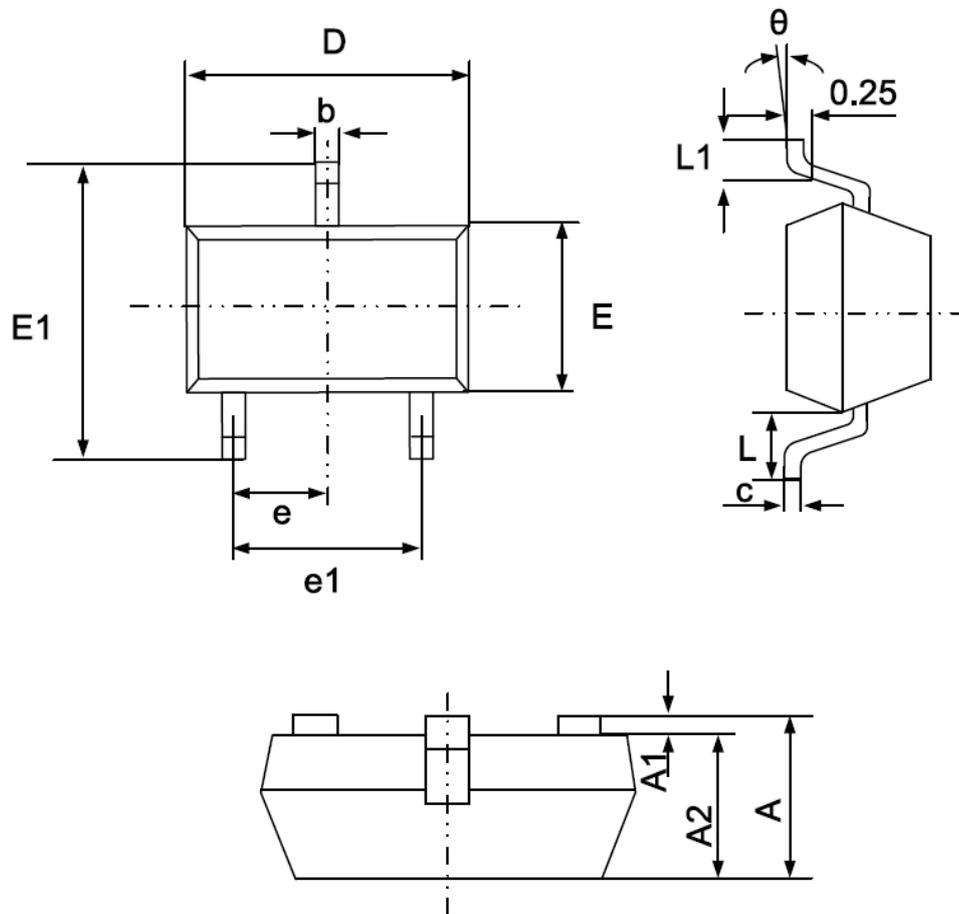


3. Forbidden Circuits



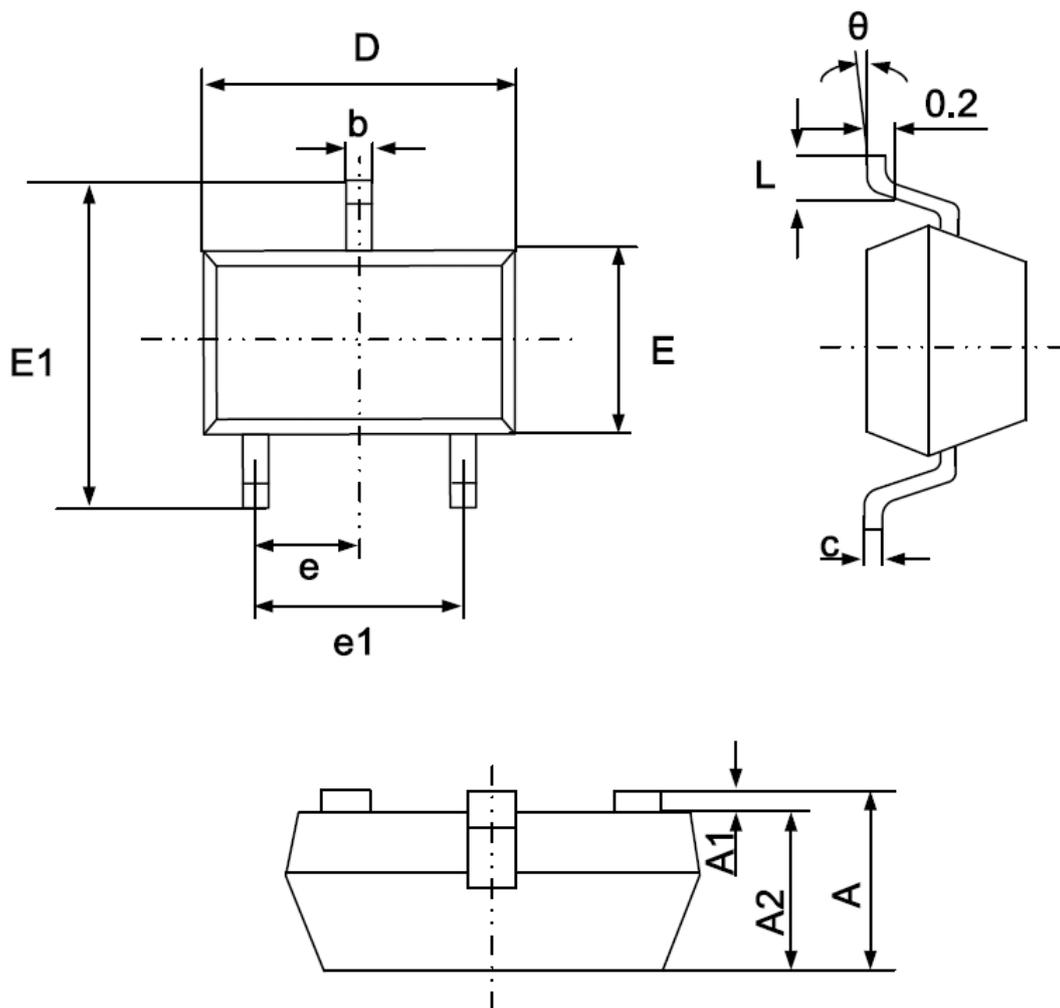
■ PACKAGING INFORMATION

● SOT-23



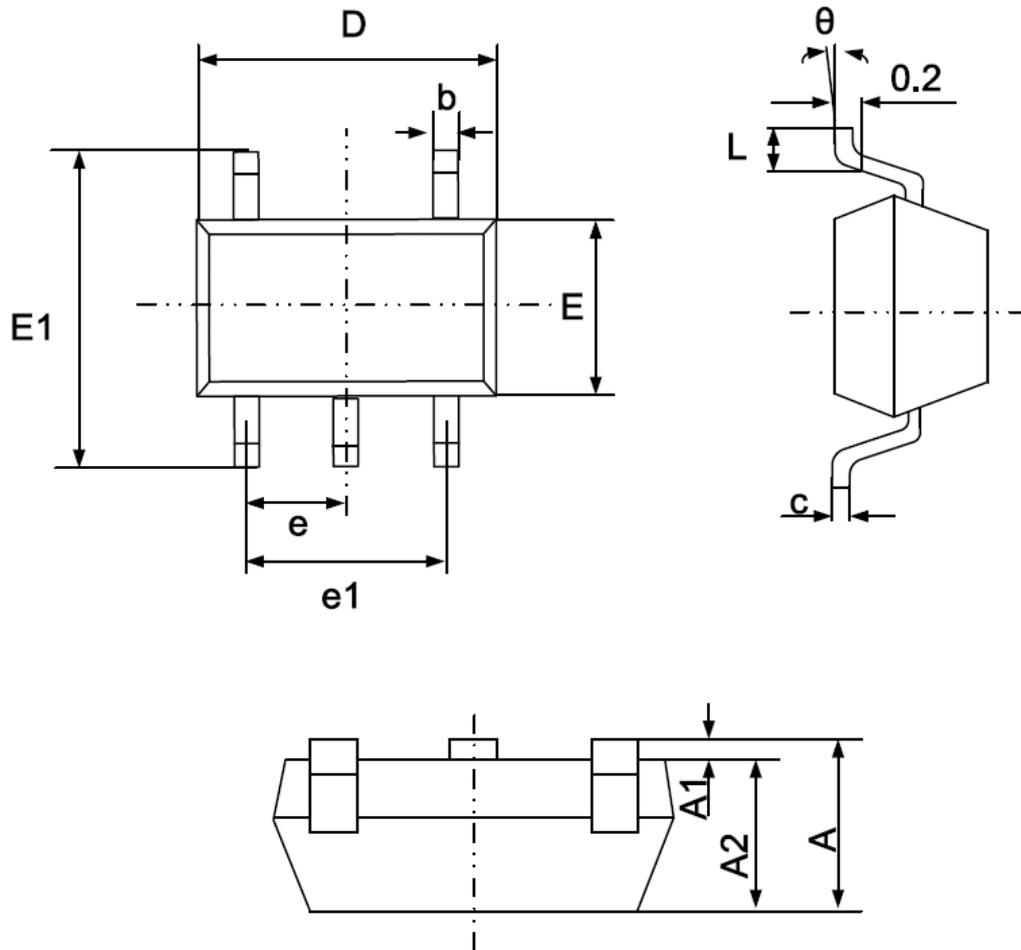
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

• SOT-23-3



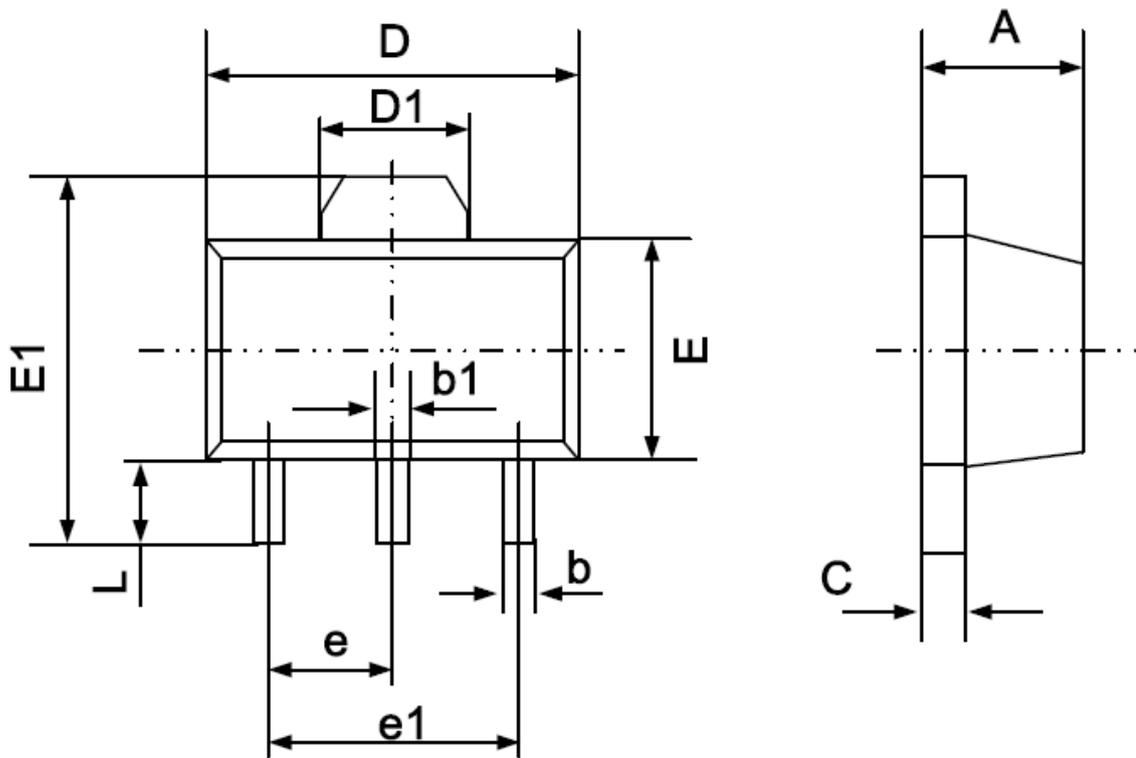
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

• SOT-23-5



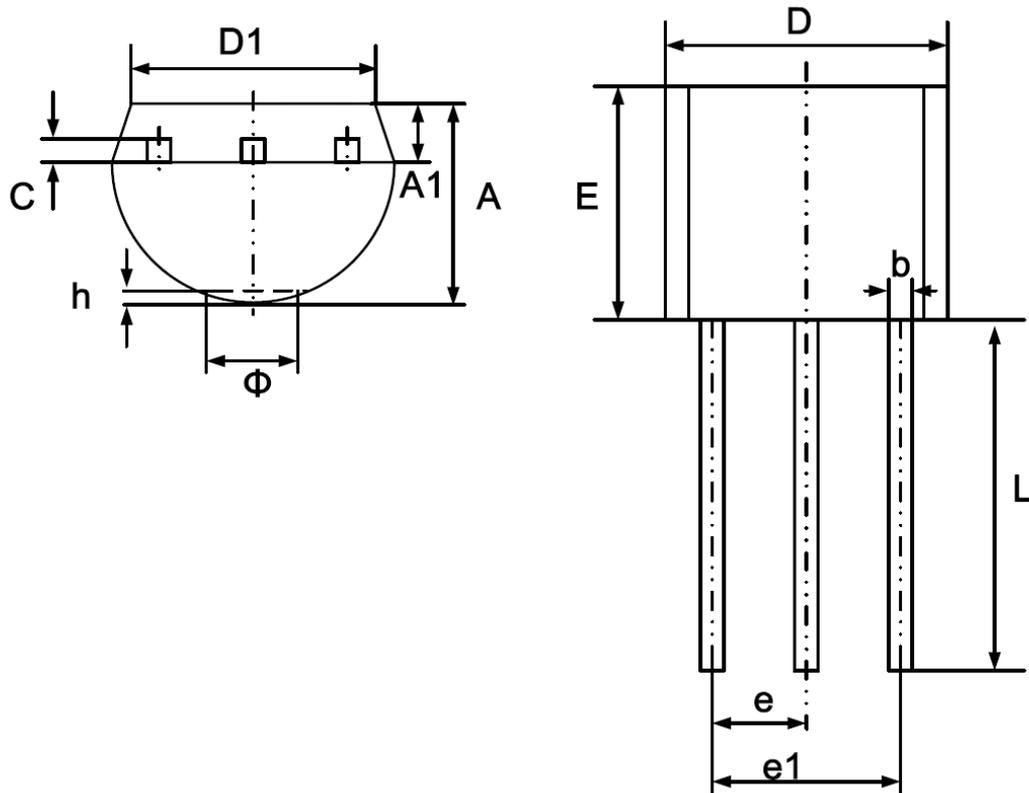
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

• SOT-89-3



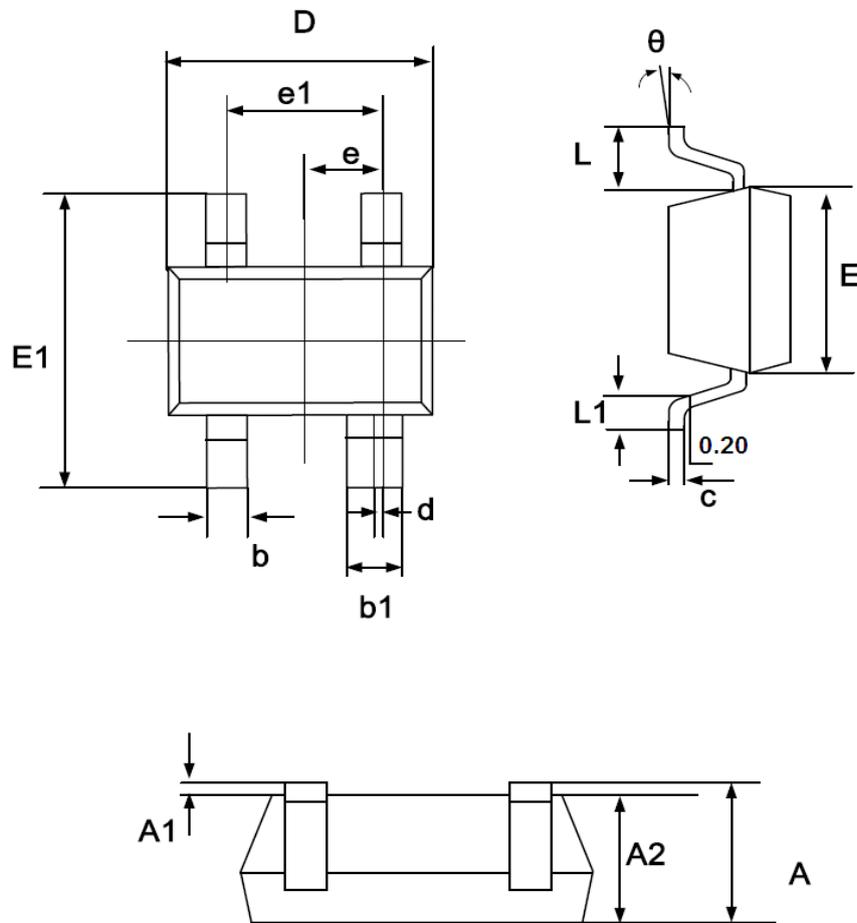
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF		0.061 REF	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP		0.060 TYP	
e1	3.000 TYP		0.118 TYP	
L	0.900	1.200	0.035	0.047

• TO-92



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	3.300	3.800
A1	1.100	1.400
b	0.380	0.600
c	0.300	0.500
D	4.400	4.800
D1	3.430	
E	4.300	4.700
e	1.270 TYP	
e1	2.440	2.640
L	13.00	15.00
Φ		1.600
h	0.000	0.380

• SOT-343



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.250	0.400
b1	0.350	0.500
c	0.080	0.150
d	0.050 TYP.	
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP	
e1	1.200	1.400
L	0.525 REF	
L1	0.260	0.460
θ	0°	8°

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